

## **Quarterly Reliability Monitoring Results**

## Quarters: Q1/2021 to Q4/2021

Based on structural similarity

	User Part Number					
	BAT54HGW					
ooratory	Part Description					
	Nexperia DHAM	Schottky				
ability labs	SMD package					
C-Q101 Test	Test Conditions	Duration	# Lots	# Quantity	# Rejects	
TEST						
Pre- and Post-Stress						
Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below	
	JESD22-A113					
Preconditioning		3 cycles	810	58300	0	
,						
Bias	reverse voltage <sup>13</sup>	1000 hours	116	9280	0	
T-0	JECD22 A104					
		1000	170	12500		
remperature Cycling	<u> </u>	1000 cycles	170	13600	0	
••						
		061	170	12600		
Autociave	Pressure = 203 KPa (29.7 psia)	96 nours	170	13600	0	
HOTOD	JESD22-A101					
		1000 haves	170	12600	0	
remperature Reverse Blas	· · · · · · · · · · · · · · · · · · ·	1000 Hours	170	13600	U	
TOL						
		1000 haves	170	12600	0	
Intermittent Operating Life	100 C 101 13000 Cycle3	1000 Hours	1/0	13000	U	
PSH	IESD22-Δ111					
		10 c	130	3900	0	
		10.5	130	3300	U	
Solderability	J-STD-002		363	3630	0	
i	Pre- and Post-Stress Electrical Test  PC Preconditioning  HTRB High Temperature Reverse Bias  TC Temperature Cycling  AC Autoclave  H3TRB High Humidity High Temperature Reverse Bias  IOL Intermittent Operating Life  RSH Resistance to Solder Heat SD	BAT54HGW  Poratory Part Description Nexperia DHAM SMD package  EC-Q101 Test Test Conditions  TEST Pre- and Post-Stress Electrical Test  Tamb = 25 °C  JESD22-A113 Bake Tamb = 125 °C Soak Tamb = 85 °C, RH = 85% Preconditioning Pore Soak Tamb = 85 °C, RH = 85% Preconditioning Pore Soak Tamb = 85 °C, RH = 85% Preconditioning Pore Soak Tamb = 85 °C, RH = 85% Preconditioning Pore Soak Tamb = 85 °C, RH = 85% Preconditioning Pore Soak Tamb = 85 °C, RH = 85% Preconditioning Pore Soak Tamb = 85 °C, RH = 85% Preconditioning Pore Soak Tamb = 121 °C, RH = 100 % Presure = 205 kPa (29.7 psia)  Pore Soak Tamb = 121 °C, RH = 85% Pore Soak Tamb = 121 °C, RH = 85% Preconditioning Pore Soak Tamb = 85 °C, RH = 85% Pore Soak Tamb = 121 °C, RH = 100 % Pressure = 205 kPa (29.7 psia)  Pore Soak Tamb = 85 °C, RH = 85% Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 121 °C, RH = 100 °C Pore Soak Tamb = 125 °C Pore Soak Tamb = 1	BAT54HGW   Part Description   Nexperia DHAM   Schottky	BAT54HGW   Part Description   Nexperia DHAM   Schottky	BAT54HGW   Part Description   Nexperia DHAM   Schottky	

<sup>[1]</sup> The physical limitations of Schottky diodes have to be considered (thermal runaway).

## **Calculation of FIT and MTTF**

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia					
DHAM	Schottky	9280	0	0.46	2.19E+09

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<sup>[2]</sup> The maximum applied voltage is limited by test chamber set up and does not exceed 115V.